

# Contributions to HICUM Parameter Extraction

by

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# Outline

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- Two point method for critical current  $I_{CK}$
- Two point method for model parameter THCS
- Pitfall during extraction of QP0 and C10 from Gummel plot

# Hicum Parameter Extraction

## Two Point Method for Critical Current $I_{CK}$ (1)

- Assuming  $ALHC=0$  the normalized injection width  $w$  is given by:

$$i = 1 - \frac{I_{CK}}{I_{TF}} \quad \rightarrow \quad w = \frac{w_I}{w_C} = \frac{i + \sqrt{i^2 + ALHC}}{1 + \sqrt{1 + ALHC}} \quad \rightarrow \quad w = i$$

- Merging both base and collector transit time parts  $\Delta T_{FB}$  and  $T_{FCT}$  results in:

$$\Delta T_{FB} = (1 - FTHC) \cdot THCS \cdot w^2 \left[ 1 + \frac{2}{\frac{I_{TF}}{I_{CK}} \sqrt{i^2 + ALHC}} \right]$$

$$T_{FCT} = FTHC \cdot THCS \cdot w^2 \left[ 1 + \frac{2}{\frac{I_{TF}}{I_{CK}} \sqrt{i^2 + ALHC}} \right]$$

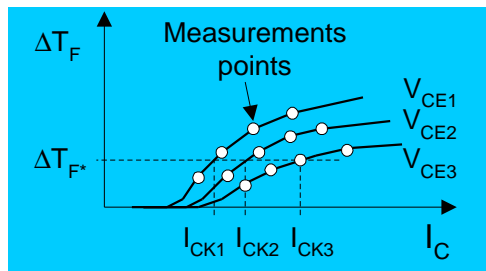
$$T_{FBC} = THCS \cdot w^2 \left[ 1 + \frac{2}{\frac{I_{TF}}{I_{CK}} \sqrt{i^2 + ALHC}} \right]$$

# Hicup Parameter Extraction

## Two Point Method for Critical Current $I_{CK}$ (2)

- $I_{TF}$  is given here by the measured  $I_C$ . There are two unknowns in second equ., the critical current  $I_{CK}$  and model parameter THCS.
- Using a plot  $\sqrt{(\Delta T_{FB} / THCS) - 1}$  vs.  $I_{CK} / I_{TF}$  we may vary THCS until the characteristic is a straight line and extract  $I_{CK}$  from slope.
- However, the better way is to use the two point equation.

$$T_{FBC} = THCS \cdot w^2 \left[ 1 + \frac{2}{\frac{I_{TF}}{I_{CK}} \sqrt{i^2 + ALHC}} \right] \rightarrow \frac{\Delta T_F}{THCS} = 1 - \left( \frac{I_{CK}}{I_{TF}} \right)^2$$

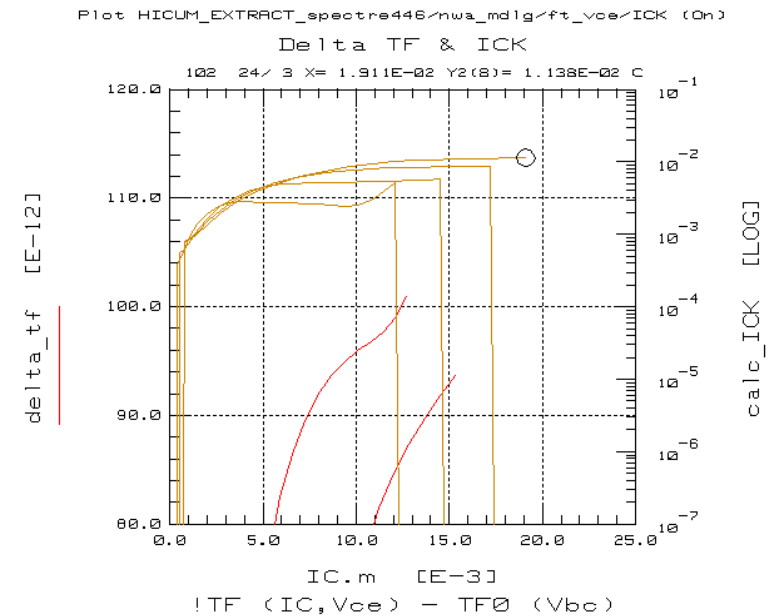
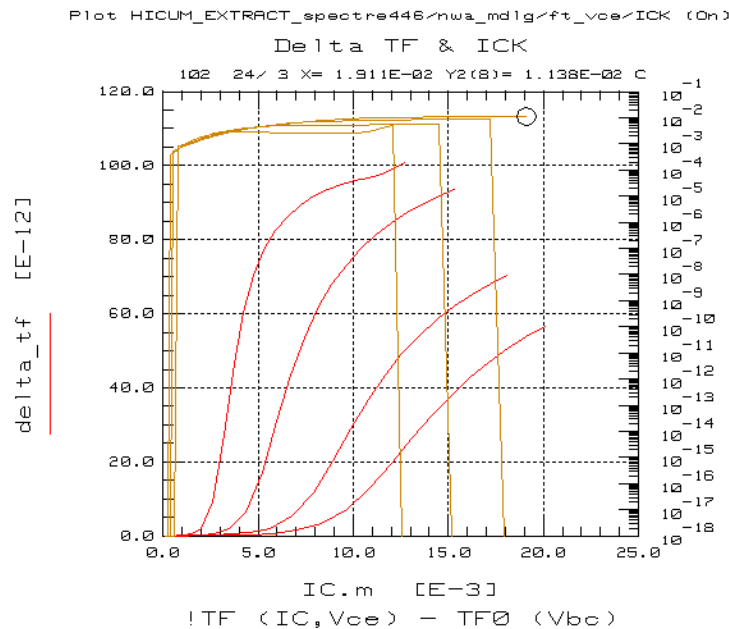


$$I_{CK} = \sqrt{\frac{\frac{\Delta T_{F2} - \Delta T_{F1}}{I_{C1}^2} - \frac{\Delta T_{F2} - \Delta T_{F2}}{I_{C2}^2}}{\frac{\Delta T_{F2} - \Delta T_{F2}}{I_{C2}^2} - \frac{\Delta T_{F1} - \Delta T_{F1}}{I_{C1}^2}}} = \sqrt{\frac{(\Delta T_{F2} - \Delta T_{F1}) I_{C1}^2 \cdot I_{C2}^2}{\Delta T_{F2} I_{C2}^2 - \Delta T_{F1} I_{C1}^2}}$$

# Hicum Parameter Extraction

## Two Point Method for Critical Current $I_{CK}$ (3)

- Extracted  $I_{CK}$  values are lower than values by Ardouin's method



$V_C / V$	0.3	0.5	1	2
$I_{CK} / \text{mA}$ (Ardouin)	4.1	7.75	13.6	20.1
$I_{CK} / \text{mA}$ (Berkner)	2.65	5.79	8.77	11.38

Note: This example is based on the model file HICUM\_EXTRACT (July 2001) from B.Ardouin (UNI Bordeaux) and the appropriate (synthetic) data in the setup nwa\_md1grft\_vce.

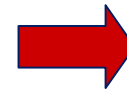
# Hicup Parameter Extraction

## Two Point Method for Model Parameter THCS (1)

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- The same principle may be used for THCS

$$T_{FBC} = THCS \cdot w^2 \left[ 1 + \frac{2}{\frac{I_{TF}}{I_{CK}} \sqrt{i^2 + ALHC}} \right]$$



$$\frac{\Delta T_F}{THCS} = 1 - \left( \frac{I_{CK}}{I_{TF}} \right)^2$$



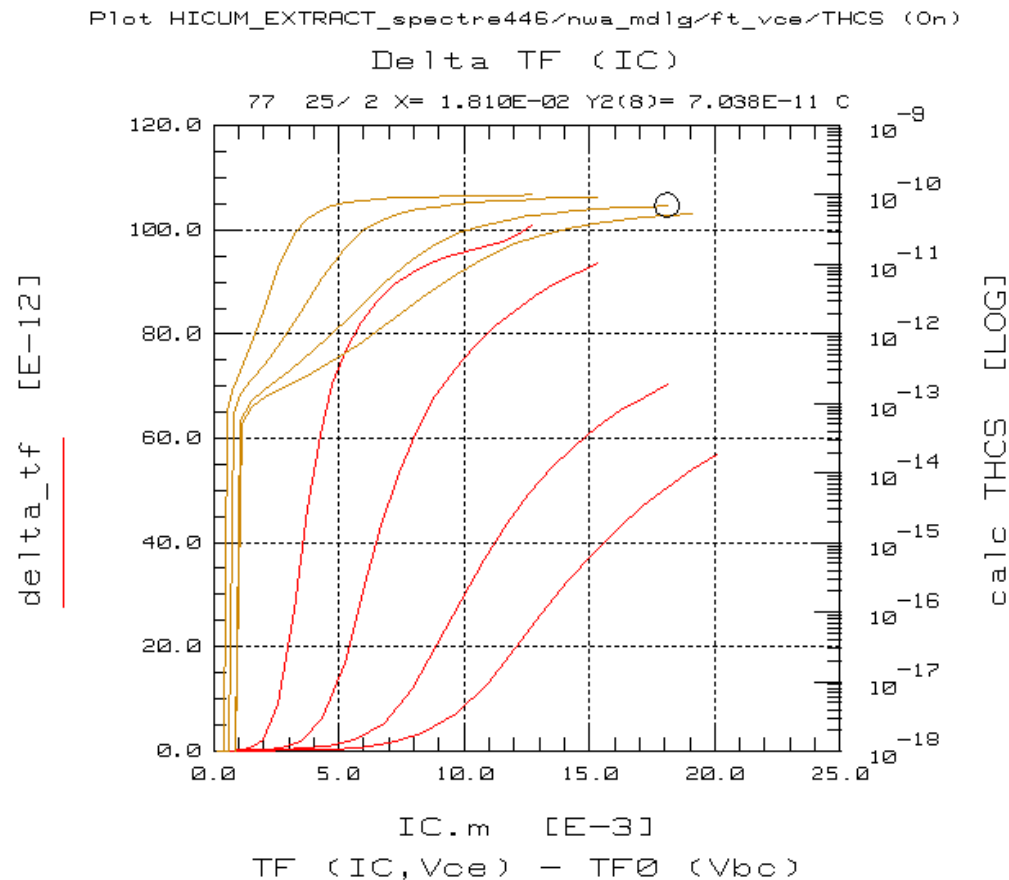
- Using two measurement points  $(\Delta T_{FB1} ; I_{C1})$  and  $(\Delta T_{FB2} ; I_{C2})$  we have:

$$THCS = \frac{\Delta T_{F1} - \Delta T_{F2} \left( \frac{I_{C2}}{I_{C1}} \right)^2}{1 - \left( \frac{I_{C2}}{I_{C1}} \right)^2}$$

# Hicum Parameter Extraction

## Two Point Method for Model Parameter THCS (2)

- The parameter THCS shows asymptotically behavior too.
- The value for the curve  $V_{CE} = 1V$  is  $THCS = 70.38pS$ .
- This is in accordance with the value  $THCS = 70 pS$  used for creating the synthetic data.



# Hicum Parameter Extraction

## Model Parameters QP0 and C10 (1)

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- QP0 and C10 may be extracted from Gummel plot measured at  $V_{BC}=0$  using an optimization

- The calculated quantity is given by:

$$\left( \frac{C10}{Q_{PT}} \right)_{meas} = \frac{I_{Cmeas}}{\exp\left(\frac{V_{BE}}{V_T}\right)}$$



Optimization



- The measured quantity is given by:

$$\left( \frac{C10}{Q_{PT}} \right)_{calc} = \frac{C10}{QP0 + Q_{JE}}$$

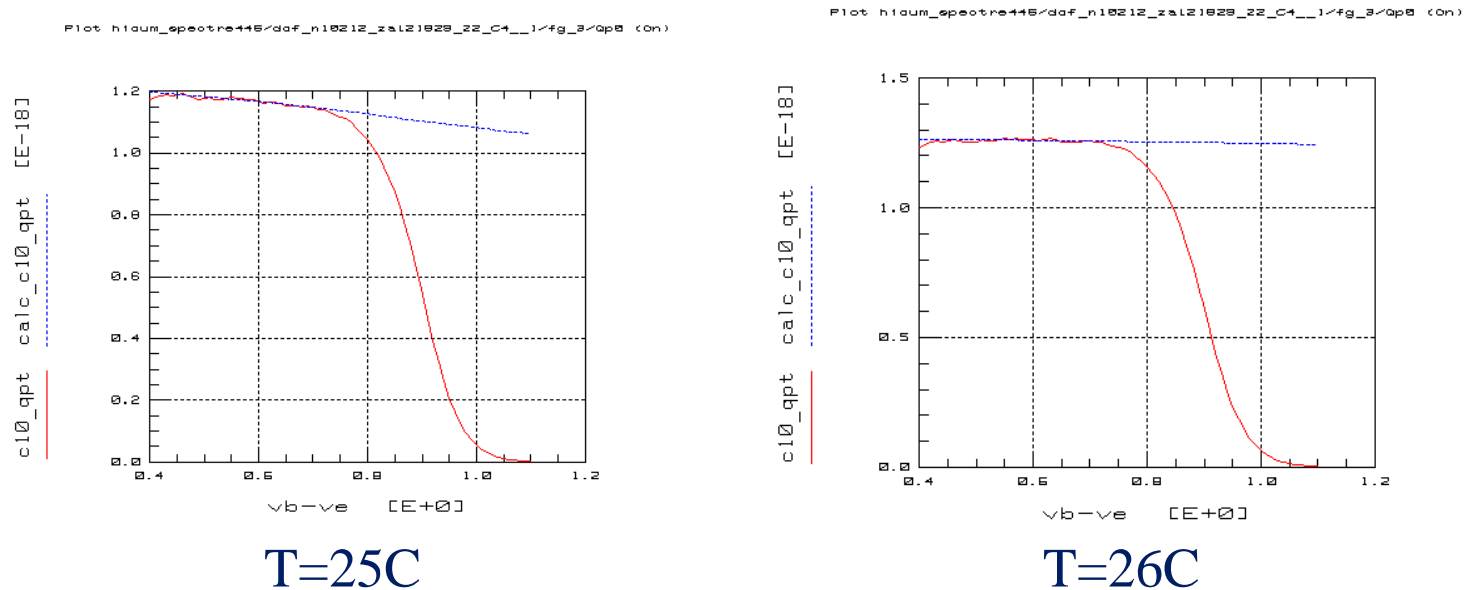
- However, the real device temperature effects via  $V_T$  very strong the QP0 and C10 values, extracted from Gummel plot



# Hicum Parameter Extraction

## Model Parameters QP0 and C10 (2)

- Pitfall: a small  $\Delta T$  results in a large  $\Delta QP0$
- Conclusion: the actual device temperature must be known and used for  $V_T$  calculation as accurate as possible



T_celcius	T_kelvin	k	q	vt	c10	qp0
24	297.15	1.38E-23	1.602E-19	0.02559719	8.00E-32	6.60E-14
25	298.15	1.38E-23	1.602E-19	0.02568333	1.66E-31	1.34E-13
26	299.15	1.38E-23	1.602E-19	0.02576948	1.41E-30	1.13E-12